VS-HFA16PB120-N3

Vishay Semiconductors

RoHS

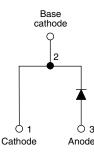
COMPLIANT

HALOGEN

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



www.vishay.com



PRIMARY CHARACTERISTICS					
I _{F(AV)}	16 A				
V _R	1200 V				
V _F at I _F	2.3 V				
t _{rr} typ.	30 ns				
T _J max.	150 °C				
Package	TO-247AC 2L				
Circuit configuration	Single				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PB120 ... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	16			
Single pulse forward current	I _{FSM}	t _p = 10 ms	190	А		
Maximum repetitive forward current	I _{FRM}		64			
Movimum neuror discinction	Р	T _C = 25 °C	151	W		
Maximum power dissipation	P _D	T _C = 100 °C	60	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

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SHAY

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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
		I _F = 16 A		-	2.5	3.0	v
Maximum forward voltage	orward voltage V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7	
Maximum reverse		$V_R = V_R$ rated	See fig. 0	-	0.75	20	
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	375	2000	μA
Junction capacitance	CT	V _R = 200 V See fig. 3		-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 - r		nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	30	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	90	135	ns
,	t _{rr2}	T _J = 125 °C		-	164	245	
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/µs V _R = 200 V	-	5.8	10	A
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	ne
Peak rate of fall of recovery		-	120	-	A∕µs		
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	76	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.83		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-		
Waight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC 2L	HFA16PB120				

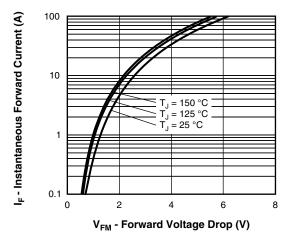
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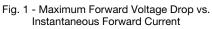
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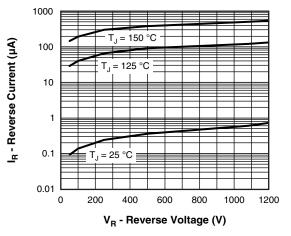


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

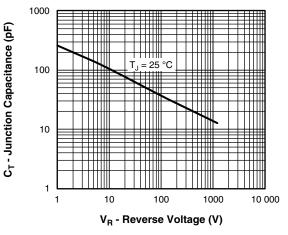


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

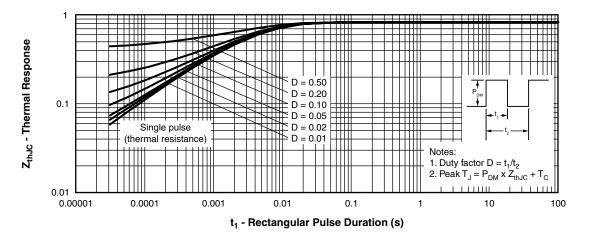


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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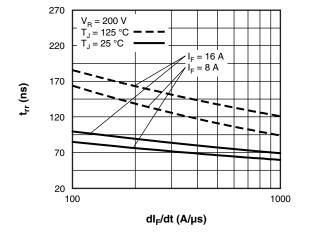


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

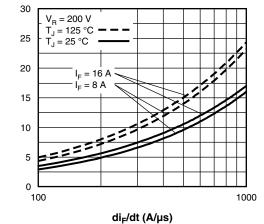


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

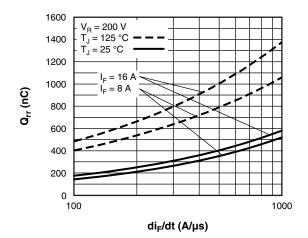


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

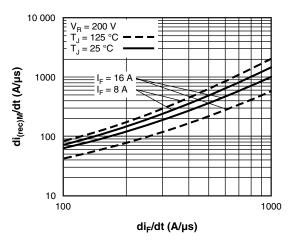


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

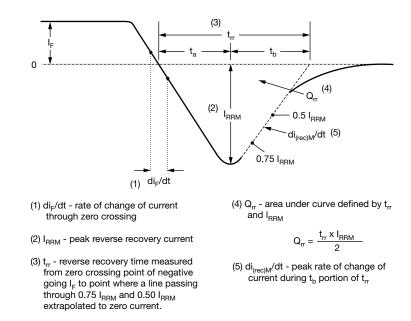


Fig. 9 - Reverse Recovery Waveform and Definitions

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I_{RR} (A)

VS-HFA16PB120-N3

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ORDERING INFORMATION TABLE

						120	-N3
(*		2	3	4	5	6	7
1 2 3 4 5 6 7	- - - -	HE) Elec Cur PB Volt Env	XFRED [®] ctron irra rent rati = TO-24 cage rati ironmer		= 16 A) pins) = 1200) V)	

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA16PB120-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96144				
Part marking information	www.vishay.com/doc?95648			



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